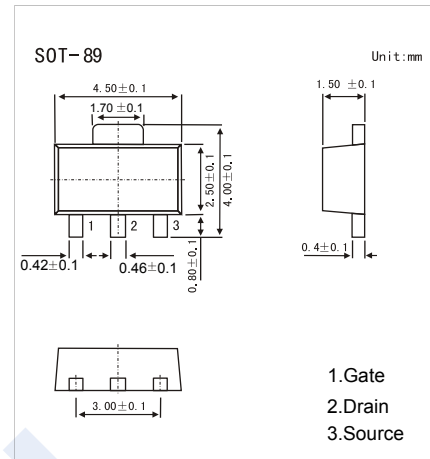
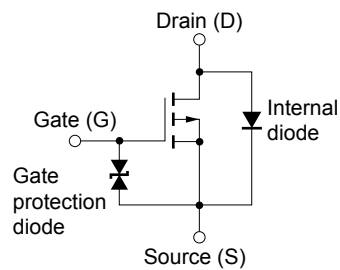


## P-Channel MOSFET

### 2SJ356

#### ■ Features

- $V_{DS} (V) = -60V$
- $I_D = -2 A (V_{GS} = -10V)$
- $R_{DS(ON)} < 0.5 \Omega (V_{GS} = -10V)$
- $R_{DS(ON)} < 0.95 \Omega (V_{GS} = -4V)$



#### ■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	-60	V
Gate-Source Voltage	$V_{GS}$	-20,+10	
Continuous Drain Current	$I_D$	-2	A
Pulsed Drain Current (Note.1)	$I_{DM}$	-4	
Power Dissipation	$P_D$	2	W
Junction Temperature	$T_J$	150	$^\circ C$
Junction Storage Temperature Range	$T_{stg}$	-55 to 150	

Note.1:  $PW \leq 10 \text{ ms}$ , duty cycle  $\leq 1\%$

## P-Channel MOSFET

### 2SJ356

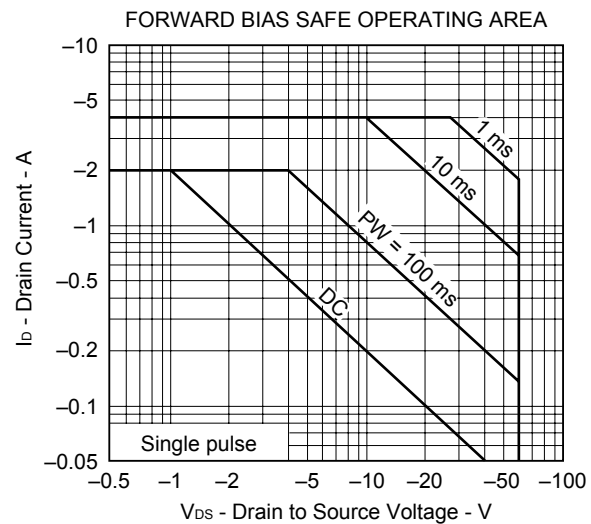
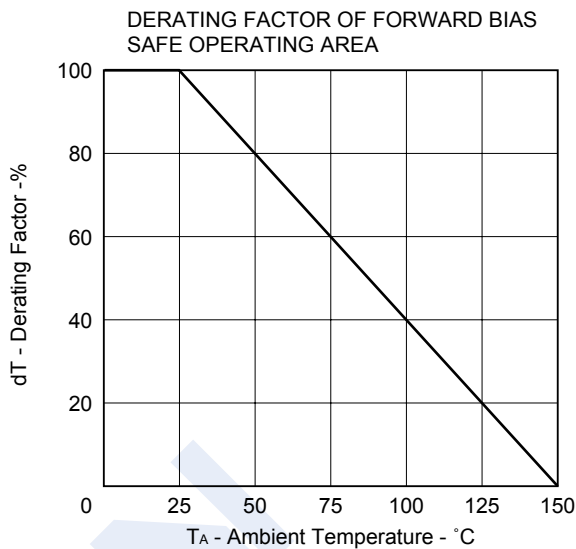
#### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V <sub>DSS</sub>	I <sub>D</sub> =-250 μA, V <sub>GS</sub> =0V	-60			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-60V, V <sub>GS</sub> =0V			-10	μA
Gate-Body leakage current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±16V			±10	μA
Gate to Source Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>GS</sub> =-10V I <sub>D</sub> =-1mA	-1		-2	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-1A			0.5	Ω
		V <sub>GS</sub> =-4V, I <sub>D</sub> =-1A			0.95	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1A	1			S
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =-10V, f=1MHz		270		pF
Output Capacitance	C <sub>oss</sub>			145		
Reverse Transfer Capacitance	C <sub>rss</sub>			55		
Gate Input Charge	Q <sub>G</sub>	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-48V, I <sub>D</sub> =-2A, I <sub>G</sub> =-2mA		11.6		nC
Gate to Source Charge	Q <sub>GS</sub>			1		
Gate to Drain Charge	Q <sub>GD</sub>			3.8		
Turn-On DelayTime	t <sub>d(on)</sub>	V <sub>GS(on)</sub> =-10V, I <sub>D</sub> =-1A, R <sub>L</sub> =25 Ω, R <sub>G</sub> =10Ω, V <sub>DD</sub> =-25V		4.3		ns
Turn-On Rise Time	t <sub>r</sub>			21		
Turn-Off DelayTime	t <sub>d(off)</sub>			115		
Turn-Off Fall Time	t <sub>f</sub>			75		
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =-2A, di/dt=50A/μs		82		nC
Internal Diode Reverse Recovery Ch	Q <sub>rr</sub>			94		

#### ■ Marking

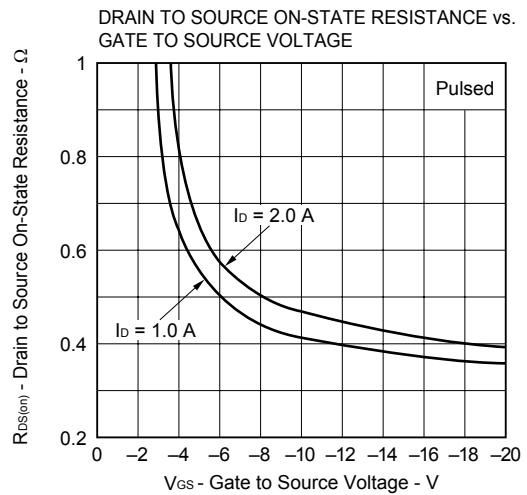
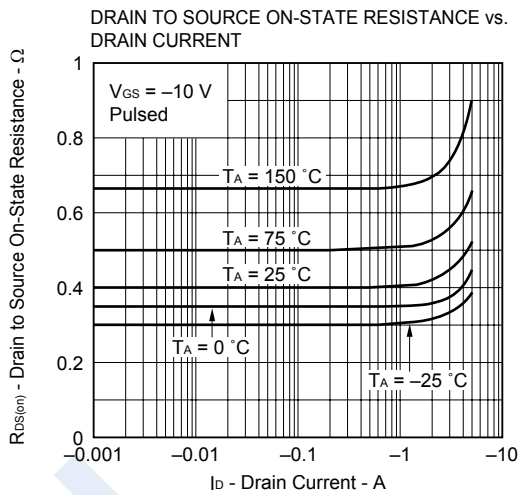
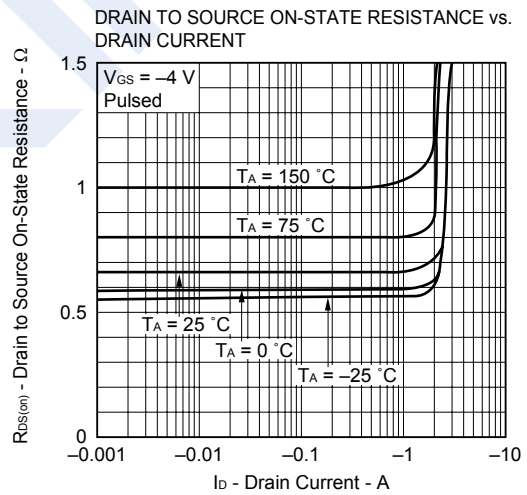
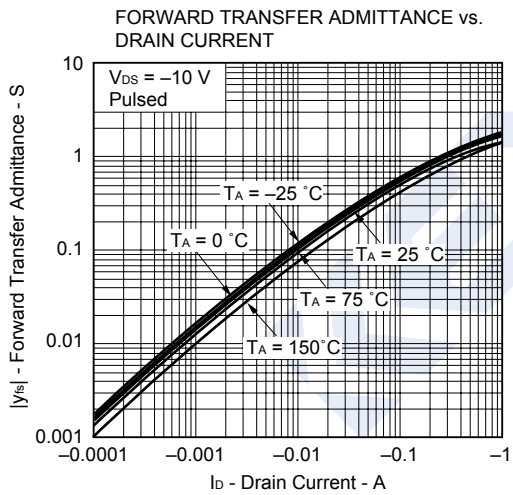
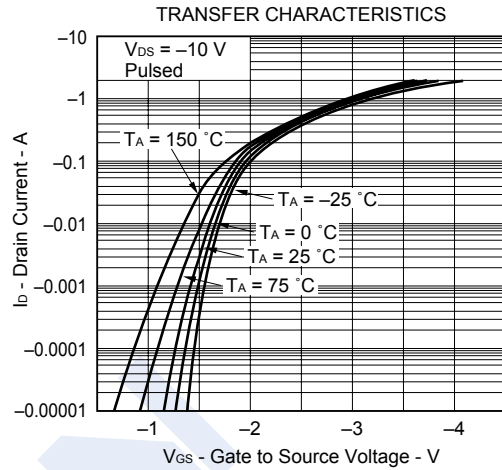
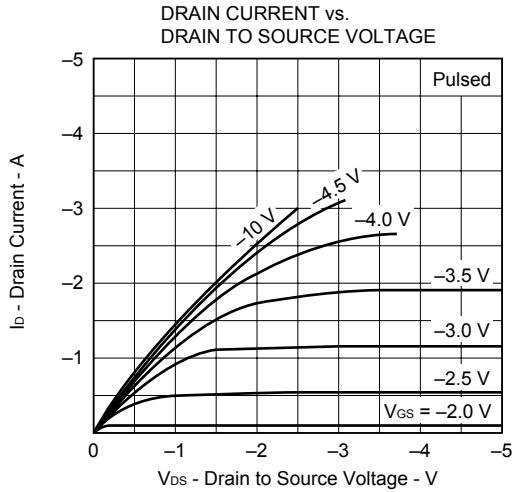
Marking	PR
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#### ■ Typical Characteristics



## P-Channel MOSFET 2SJ356

■ Typical Characteristics



## P-Channel MOSFET

### 2SJ356

#### Typical Characteristics

